10A, 35V - 200V Schottky Barrier Rectifier

FEATURES

TAIWAN

• AEC-Q101 qualified available

SEMICONDUCTOR

- Low power loss, high efficiency
- Guard ring for overvoltage protection
- High surge current capability
- RoHS Compliant
- Halogen-free according to IEC 61249-2-21

APPLICATIONS

- Switching mode power supply (SMPS)
- Adapters
- DC to DC converters

MECHANICAL DATA

- Case: TO-220AC
- Molding compound meets UL 94V-0 flammability rating
- Terminal: Matte tin plated leads, solderable per J-STD-002
- Mounting torque: 0.56 N·m maximum
- Meet JESD 201 class 2 whisker test
- Polarity: As marked
- Weight: 1.88g (approximately)

KEY PARAMETERS				
PARAMETER	VALUE	UNIT		
I _F	10	А		
V _{RRM}	35 - 200	V		
I _{FSM}	150	А		
T _{J MAX}	150	°C		
Package	TO-220AC			
Configuration	Single die			







ABSOLUTE MAXIMUM I	RATINGS ($T_A = 25^{\circ}C$	C unless	otherwis	se noted))				
PARAMETER	SYMBOL	MBR 1035	MBR 1045	MBR 1050	MBR 1060	MBR 1090	MBR 10100	MBR 10150	MBR 10200	υνιτ
Marking code on the device		MBR 1035	MBR 1045	MBR 1050	MBR 1060	MBR 1090	MBR 10100	MBR 10150	MBR 10200	
Repetitive peak reverse voltage	V_{RRM}	35	45	50	60	90	100	150	200	V
Reverse voltage, total rms value	$V_{R(RMS)}$	24	31	35	42	63	70	105	140	V
Forward current	I _F		10					Α		
Surge peak forward current 8.3ms single half sine wave superimposed on rated load	I _{FSM}	150				А				
Peak repetitive forward current (Rated V _R , Square Wave, 20KHz)	I _{FRM}	20				A				
Peak repetitive reverse surge current ⁽¹⁾	I _{RRM}	1 0.5				Α				
Voltage rate of change (Rated V _R)	dV/dt				10,	000				V/µs

MBR1035 – MBR10200

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MBR1035 – MBR10200 Taiwan Semiconductor

ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise noted)										
PARAMETER	SYMBOL	MBR 1035	MBR 1045	MBR 1050	MBR 1060	MBR 1090	MBR 10100	MBR 10150	MBR 10200	υνιτ
Junction temperature	TJ		1035 1045 1050 1060 1090 10100 10150 10200 -55 to +150			°C				
Storage temperature	T _{STG}	-55 to +175			°C					

Notes:

1. $tp = 2.0\mu s$, 1.0KHz

THERMAL PERFORMANCE	-		
PARAMETER	SYMBOL	ТҮР	UNIT
Junction-to-case resistance	R _{eJC}	3	°C/W

ELECTRICAL SPECIFI	CATIONS	$(T_A = 25^{\circ}C \text{ unless otherwise})$	erwise noted)			
PARAMETER		CONDITIONS	SYMBOL	ТҮР	МАХ	UNIT
	MBR1035 MBR1045	I _F = 10A, T _⊥ = 25°C		-	0.70	V
	MBR1050 MBR1060			-	0.80	V
	MBR1090 MBR10100	IF - 10A, 1J - 20 0		-	0.85	V
Forward voltage ⁽¹⁾	MBR10150 MBR10200			-	1.05	V
Forward voltage	MBR1035 MBR1045		ν _F	-	0.57	V
	MBR1050 MBR1060			-	0.70	V
	MBR1090 MBR10100			-	0.71	V
	MBR10150 MBR10200			-	-	V
Reverse current @ rated V _R ⁽²⁾	MBR1035 MBR1045 MBR1050 MBR1060 MBR1090 MBR10100 MBR10150	TJ = 25°C		-	100	μΑ
	MBR1035 MBR1045		I _R	-	15	mA
	MBR1050 MBR1060	T _J = 125°C		-	10	mA
	MBR1090 MBR10100 MBR10150 MBR10200			-	6	mA

Notes:

1. Pulse test with PW = 0.3ms

2. Pulse test with PW = 30ms



ORDERING INFORMATION

	1	
ORDERING CODE ⁽¹⁾⁽²⁾	PACKAGE	PACKING
MBR10x	TO-220AC	50 / Tube
MBR10xH	TO-220AC	50 / Tube

Notes:

1. "x" defines voltage from 35V(MBR1035) to 200V(MBR10200)

2. "H" means AEC-Q101 qualified



10

REVERSE VOLTAGE (V)

Fig.4 Typical Forward Characteristics

100

CHARACTERISTICS CURVES

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$

Fig.1 Forward Current Derating Curve

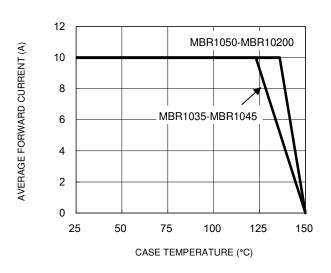
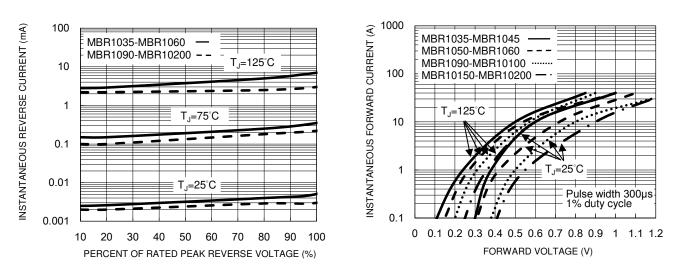


Fig.3 Typical Reverse Characteristics



10000

1000

100

0.1

f=1.0MHz Vsig=50mVp-p

1

CAPACITANCE (pF)

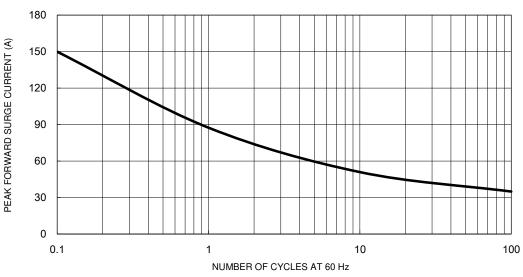


Fig.5 Maximum Non-Repetitive Forward Surge Current

Fig.2 Typical Junction Capacitance



CHARACTERISTICS CURVES

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$

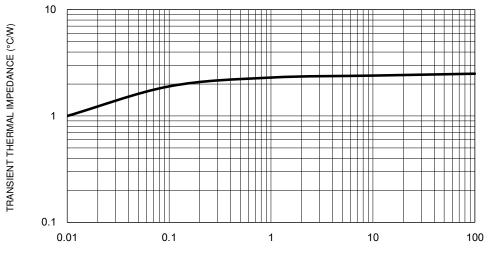


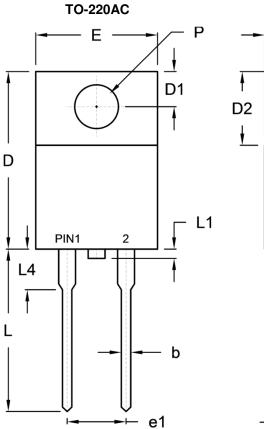
Fig.6 Typical Transient Thermal Impedance

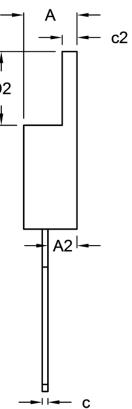
PULSE DURATION (s)

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PACKAGE OUTLINE DIMENSIONS





DIM.	Unit	Unit (mm)		(inch)
	Min.	Max.	Min.	Max.
A	4.42	4.76	0.174	0.187
A2	2.20	2.80	0.087	0.110
b	0.68	0.94	0.027	0.037
с	0.35	0.64	0.014	0.025
c2	1.14	1.40	0.045	0.055
D	14.60	16.00	0.575	0.630
D1	2.62	3.44	0.103	0.135
D2	5.84	6.86	0.230	0.270
E	-	10.50	-	0.413
e1	4.95	5.20	0.195	0.205
L	13.19	14.79	0.519	0.582
L1	0.00	1.60	0.000	0.063
L4	2.80	4.20	0.110	0.165
Р	3.54	4.00	0.139	0.157

MARKING DIAGRAM



P/N	= Marking Code
G	= Green Compound
YWW	= Date Code
F	= Factory Code



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